

1N4448W

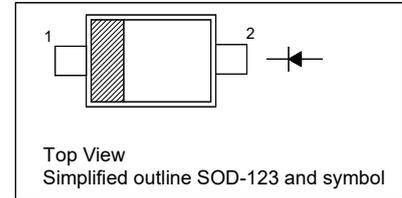
Silicon Epitaxial Planar Switching Diode

Features

- Fast Switching Diode

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Cathode |
| 2 | Anode |



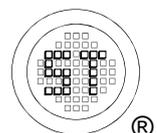
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|--|-------------|---------------|------------------|
| Peak Reverse Voltage | V_{RM} | 100 | V |
| Reverse Voltage | V_R | 80 | V |
| Average Rectified Forward Current | $I_{F(AV)}$ | 150 | mA |
| Forward Continuous Current | I_{FM} | 300 | mA |
| Non-Repetitive Peak Forward Surge Current (at $t = 1\text{ }\mu\text{s}$) | I_{FSM} | 4 | A |
| Power Dissipation | P_d | 400 | mW |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 65 to + 150 | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Max. | Unit |
|---|-----------------|------|--------------------|
| Thermal Resistance from Junction to Ambient ¹⁾ | $R_{\theta JA}$ | 313 | $^\circ\text{C/W}$ |

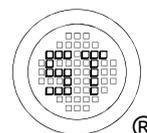
¹⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



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Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Min. | Max. | Unit |
|---|-------------|---------------------|----------------------------|--|
| Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$ at $I_F = 150\text{ mA}$ | V_F | 0.62 - - - | 0.72 0.855 1 1.25 | V |
| Reverse Leakage Current at $V_R = 80\text{ V}$ at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ at $V_R = 25\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ | I_R | - - - - | 100 25 50 30 | nA nA μA μA |
| Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$ | $V_{(BR)R}$ | 80 | - | V |
| Total Capacitance at $V_R = 0.5\text{ V}$, $f = 1\text{ MHz}$ | C_{tot} | - | 4 | pF |
| Reverse Recovery Time at $I_F = 10\text{ mA}$, $I_{rr} = 0.1 \times I_R$, $V_R = 6\text{ V}$, $R_L = 100\text{ }\Omega$ | t_{rr} | - | 4 | ns |



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Electrical Characteristics Curves

Fig 1. Power Derating Curve

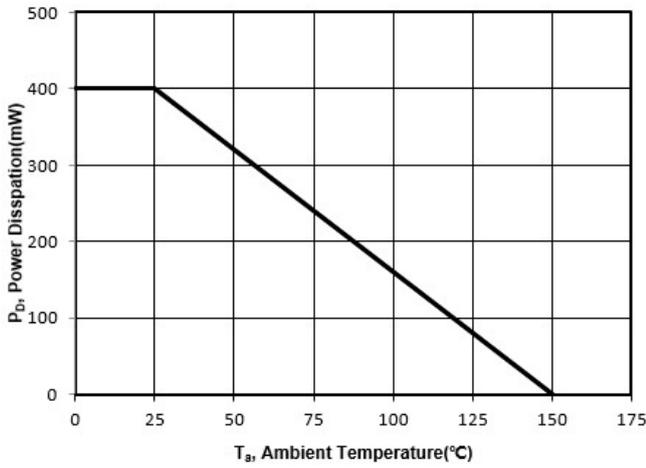


Fig 2. Total Capacitance vs. Reverse Voltage

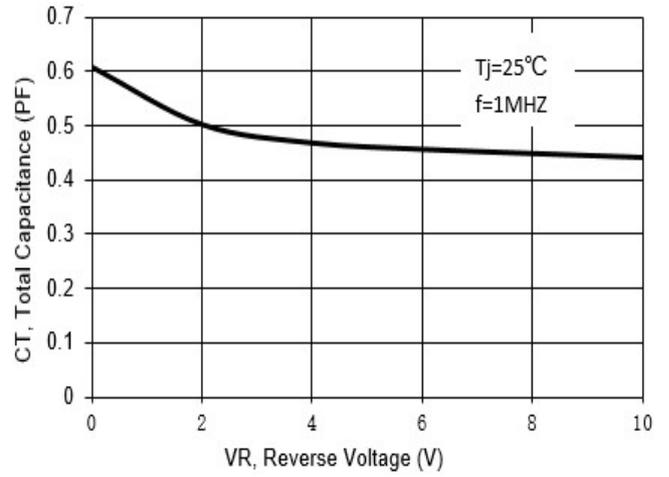


Fig 3. Reverse Current vs. Reverse Voltage

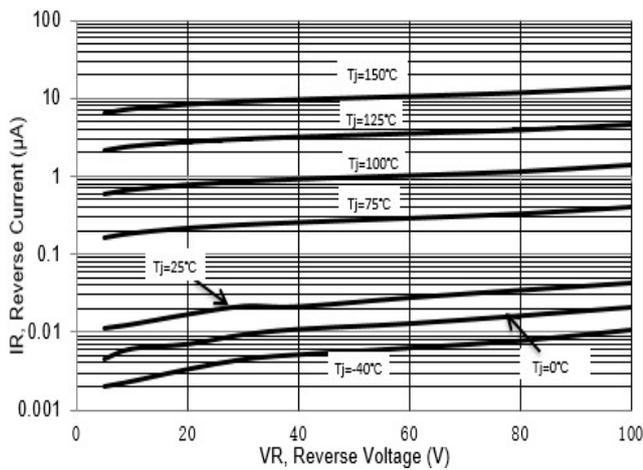
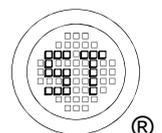
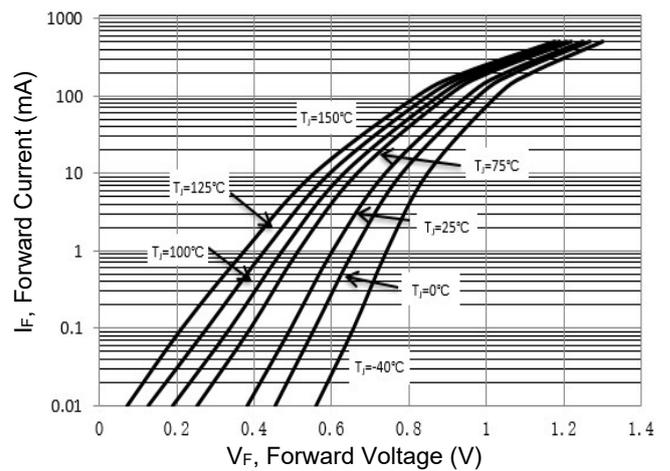


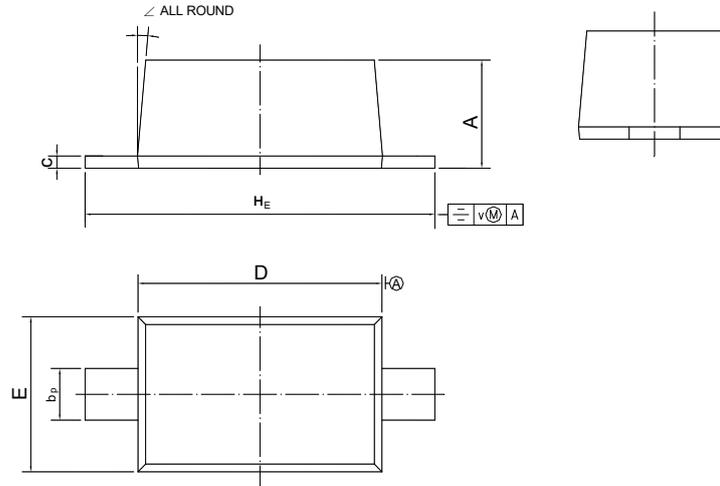
Fig 4. Forward Characteristics



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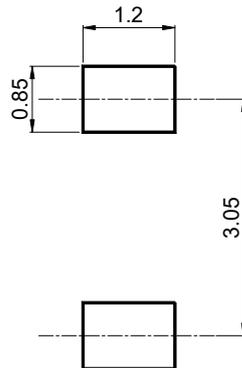
PACKAGE OUTLINE Plastic surface mounted package

SOD-123



| UNIT | A | b _p | c | D | E | H _E | v | ∠ |
|------|--------------|----------------|----------------|------------|--------------|----------------|-----|----|
| mm | 1.15 1.05 | 0.6 0.5 | 0.135 0.100 | 2.7 2.6 | 1.65 1.55 | 3.85 3.55 | 0.2 | 5° |

Recommended Soldering Footprint



Packing information

| Package | Tape Width (mm) | Pitch | | Reel Size | | Per Reel Packing Quantity |
|---------|-----------------|---------|---------------|-----------|--------|---------------------------|
| | | mm | (inch) | mm | (inch) | |
| SOD-123 | 8 | 4 ± 0.1 | 0.157 ± 0.004 | 178 | 7 | 3,000 |

Marking information

" W1 " = Part No.
" III " = Cathode line
Font type: Arial

